

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (previously presented): A sputtering target or thin film formed therefrom comprising a sputtering target or thin film made of a high purity hafnium material, wherein a zirconium content of the target or thin film is 1 to 1000wtppm, a purity of the target or thin film is 4N5 to 6N excluding gas components of carbon, oxygen and nitrogen, and the contents of oxygen being 500wtppm or less, nitrogen and carbon being respectively 100wtppm or less, and iron, chromium and nickel being respectively 10wtppm or less.

Claims 2-27 (canceled).

Claim 28 (previously presented): A sputtering target or thin film according to claim 1, wherein said purity of the target or thin film is 6N.

Claim 29 (canceled).

Claim 30 (currently amended): A hafnium sputtering target comprising:  
a sputtering target body consisting of high purity hafnium of a purity of at least  
4N5 (99.995wt%) excluding zirconium content and gas components of  
carbon, oxygen and nitrogen;

said high purity hafnium having a zirconium content of 1 to 1000wtppm, an oxygen content of 500wtppm or less, a nitrogen content of 100wtppm or less, a carbon content of 100wtppm or less, an iron content of 10wtppm or less, a chromium content of 10wtppm or less, and a nickel content of 10wtppm or less; and  
said sputtering target body having a forged and rolled microstructure having been subject to forging and rolling processing.

Claim 31 (previously presented): A hafnium sputtering target according to claim 30, wherein said purity is 6N (99.9999wt%).

Claim 32 (previously presented): A thin film formed from sputtering a hafnium sputtering target comprising:

a thin film consisting of high purity hafnium of a purity of at least 4N5 (99.995wt%) excluding zirconium content and gas components of carbon, oxygen and nitrogen;

said high purity hafnium having a zirconium content of 1 to 1000wtppm, an oxygen content of 500wtppm or less, a nitrogen content of 100wtppm or less, a carbon content of 100wtppm or less, an iron content of 10wtppm or less, a chromium content of 10wtppm or less, and a nickel content of 10wtppm or less.

Claim 33 (previously presented): A thin film according to claim 32, wherein said purity is 6N (99.9999wt%).

Claim 34 (new): A thin film according to claim 33, wherein said zirconium content is 1 to 200wtppm.

Claim 35 (new): A hafnium sputtering target according to claim 30, wherein said zirconium content throughout said sputtering target body is 1 to 200wtppm.